



# 제25회 한국반도체학술대회

The 25<sup>th</sup> Korean Conference on Semiconductors

2018년 2월 5일(월)-7일(수), 강원도 하이원리조트 컨벤션 호텔

2018년 2월 7일(수), 16:15-17:30

Room C (함백, 5층)

## D. Thin Film Process Technology 분과

### [WC4-D] Thin Films for Memories and Transistors II

좌장: 김건환(한국화학연구원), 최병준 교수(서울과학기술대학교)

<p><b>WC4-D-1</b> 16:15-16:30</p>	<p><b>Si Doping in HfO<sub>2</sub> by Atomic Layer Deposition for Ferroelectric Tunneling Junction Applications</b> Yong-Woon Lee<sup>1</sup>, Jong-Seo Park<sup>2,3</sup>, and Han-Bo-Ram Lee<sup>1,2</sup> <i><sup>1</sup>Department of Materials Science and Engineering, Incheon National University, <sup>2</sup>Innovation Center for Chemical Engineering, Incheon National University, <sup>3</sup>School of Electrical and Electronic Engineering, Yonsei University</i></p>
<p><b>WC4-D-2</b> 16:30-16:45</p>	<p><b>The Influence of High Pressure Annealing on Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> Ferroelectric Films</b> Taeho Kim and Sanghun Jeon <i>Department of Applied Physics, Korea University</i></p>
<p><b>WC4-D-3</b> 16:45-17:00</p>	<p><b>Directly Drawn Carbon Nanotube Transistors with a High Device Yield and Uniform Performance</b> Jinhee Park, Bongsik Choi, Jinsu Yoon, Yongwoo Lee, Jungmin Han, Jieun Lee, Yeamin Kim, Dong Myong Kim, Dae Hwan Kim, and Sung-Jin Choi <i>School of Electrical Engineering, Kookmin University</i></p>
<p><b>WC4-D-4</b> 17:00-17:15</p>	<p><b>Characteristics of Activation and Post-Metal Annealing Using Microwave in Phosphorus-implanted SOI MOSFETs</b> Gi-yong Lee and Won-Ju Cho <i>Department of Electronic Material Engineering, Kwangwoon University</i></p>
<p><b>WC4-D-5</b> 17:15-17:30</p>	<p><b>반도체/OLED용 화학증착소재의 열·화학적 안정성 평가</b> 심섭<sup>1,2</sup>, 안종기<sup>1</sup>, 강고루<sup>1</sup>, 강연태<sup>1</sup>, 김하영<sup>1,2</sup>, 손주희<sup>3</sup>, 김진태<sup>1,2</sup>, 정낙관<sup>1</sup>, 허규용<sup>3</sup>, 윤주영<sup>1,2</sup> <i><sup>1</sup>한국표준과학연구원 소재에너지융합측정센터, <sup>2</sup>과학기술연합대학원대학교 나노재료공학, <sup>3</sup>한국화학연구원 신뢰성평가센터</i></p>